



AO4472

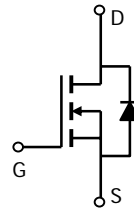
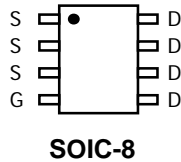
N-Channel Enhancement Mode Field Effect Transistor

General Description

The AO4472 uses advanced trench technology to provide excellent $R_{DS(ON)}$, shoot-through immunity, body diode characteristics and ultra-low gate resistance. This device is ideally suited for use as a low side switch in Notebook CPU core power conversion. *Standard Product AO4472 is Pb-free (meets ROHS & Sony 259 specifications). AO4472L is a Green Product ordering option. AO4472 and AO4472L are electrically identical.*

Features

- $V_{DS} (V) = 30V$
- $I_D = 19A (V_{GS} = 10V)$
- $R_{DS(ON)} < 5.2m\Omega (V_{GS} = 10V)$
- $R_{DS(ON)} < 7.2m\Omega (V_{GS} = 4.5V)$



Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^A	$T_A=25^\circ C$	19	A
	$T_A=70^\circ C$	16	
Pulsed Drain Current ^B	I_{DM}	80	
Power Dissipation	$T_A=25^\circ C$	3	W
	$T_A=70^\circ C$	2.1	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ C$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	31	40	$^\circ C/W$
Maximum Junction-to-Ambient ^A		Steady-State	59	
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	16	24	$^\circ C/W$

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =24V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} = ±20V			100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} I _D =250μA	1	1.9	2.5	V
I _{D(ON)}	On state drain current	V _{GS} =10V, V _{DS} =5V	80			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =19A T _J =125°C		4.3 6.1	5.2 7.5	mΩ
		V _{GS} =4.5V, I _D =15A		6	7.2	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =19A		82		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.7	1	V
I _S	Maximum Body-Diode Continuous Current				4.5	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance			6060	7270	pF
C _{oss}	Output Capacitance	V _{GS} =0V, V _{DS} =15V, f=1MHz		638	960	pF
C _{rss}	Reverse Transfer Capacitance			355	530	pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		0.45	0.9	Ω
SWITCHING PARAMETERS						
Q _g (10V)	Total Gate Charge		80	103	124	nC
Q _g (4.5V)	Total Gate Charge	V _{GS} =10V, V _{DS} =15V, I _D =19A	37	48	58	nC
Q _{gs}	Gate Source Charge			18		nC
Q _{gd}	Gate Drain Charge			15		nC
t _{D(on)}	Turn-On Delay Time			12	16	ns
t _r	Turn-On Rise Time	V _{GS} =10V, V _{DS} =15V, R _L =0.8Ω,		8	12	ns
t _{D(off)}	Turn-Off Delay Time	R _{GEN} =3Ω		51.5	70	ns
t _f	Turn-Off Fall Time			8.8	14	ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =19A, dI/dt=100A/μs		33.5	44	ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =19A, dI/dt=100A/μs		22	30	nC

A: The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design. The current rating is based on the t ≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using 80 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

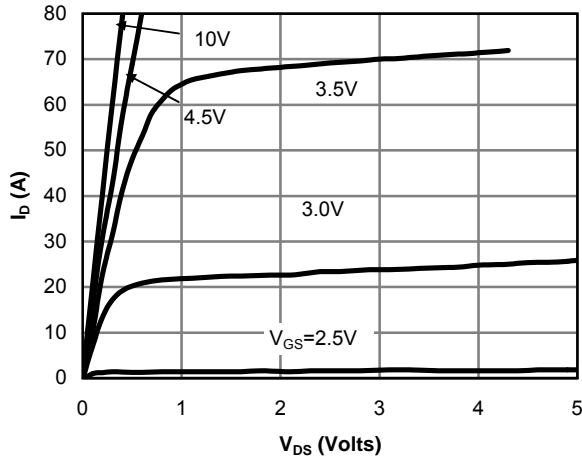


Fig 1: On-Region Characteristics

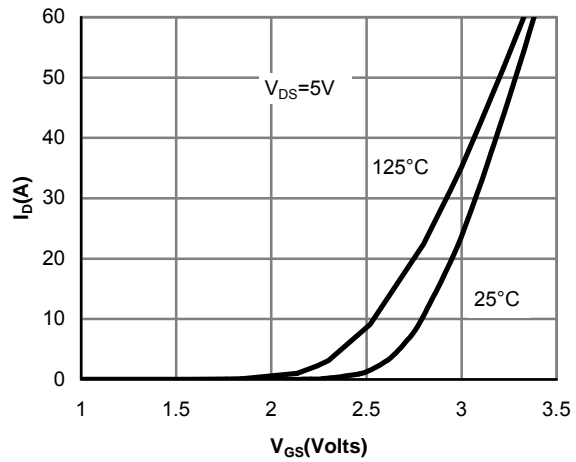


Figure 2: Transfer Characteristics

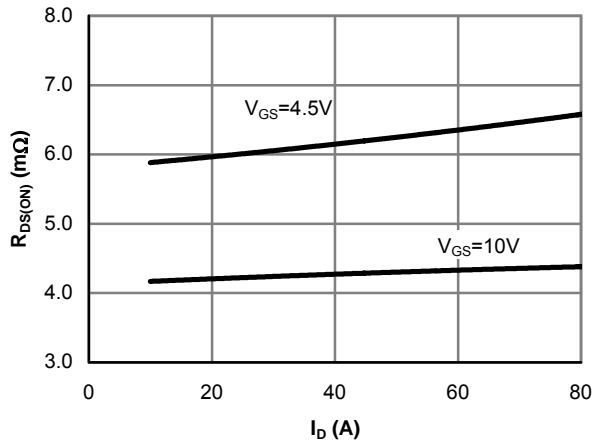


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

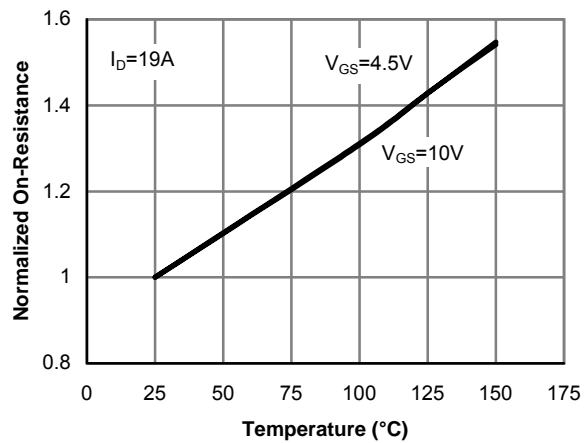


Figure 4: On-Resistance vs. Junction Temperature

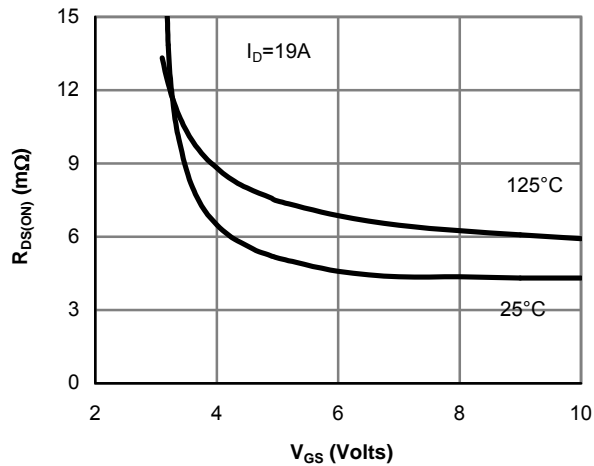


Figure 5: On-Resistance vs. Gate-Source Voltage

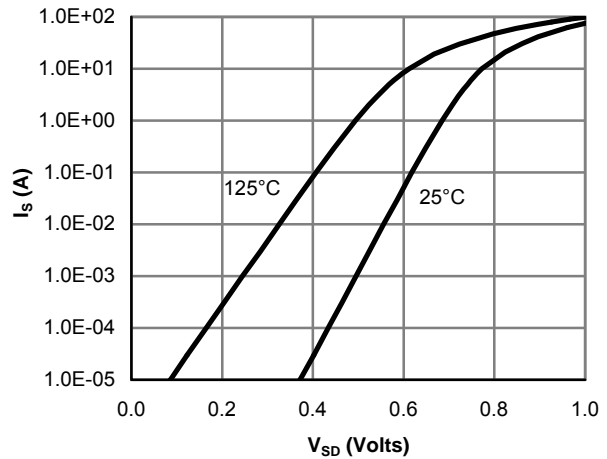


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

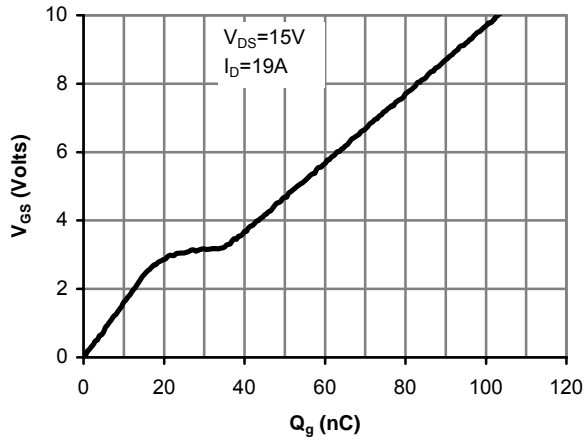


Figure 7: Gate-Charge Characteristics

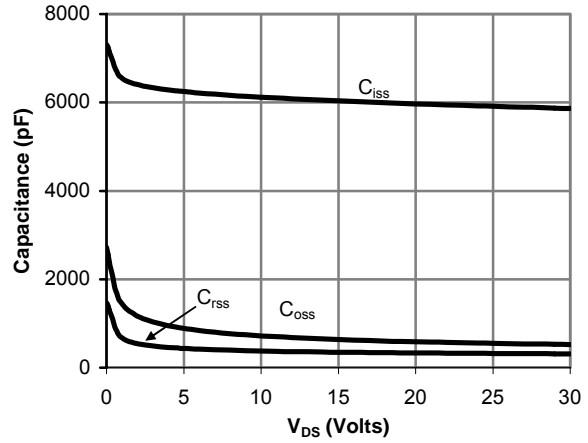


Figure 8: Capacitance Characteristics

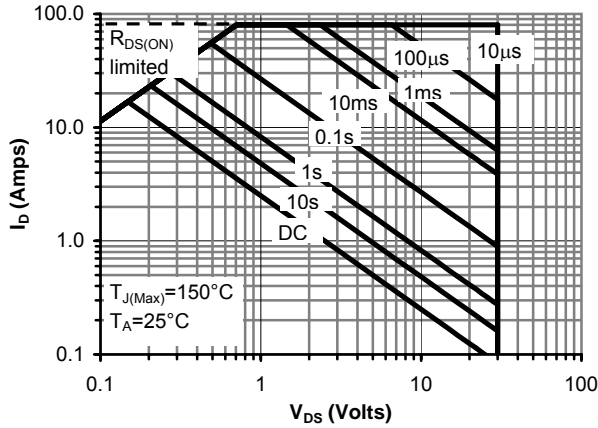


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

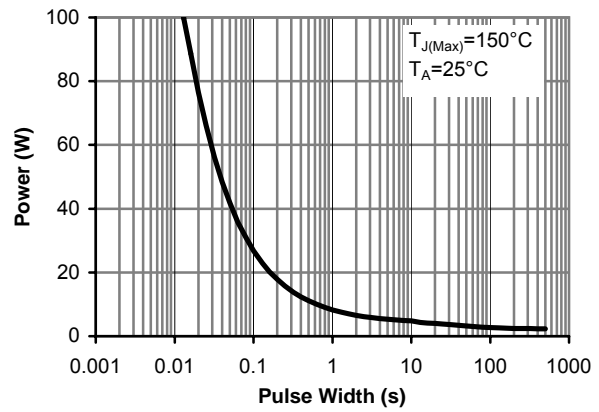


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

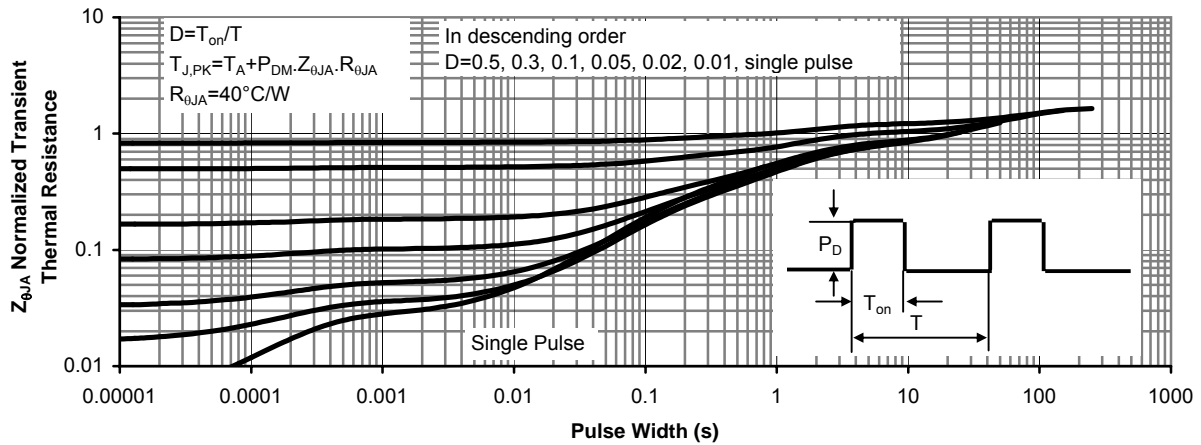


Figure 11: Normalized Maximum Transient Thermal Impedance